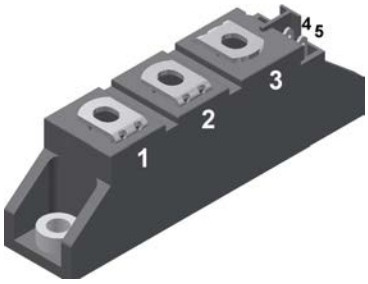
Thyristor \ Diode Module

V_{RRM}	= 2x	800 V
I_{TAV}	=	60 A
V_T	=	1,24 V

Phase leg

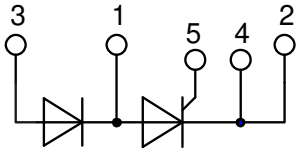
Part number

MCD56-08io1B



Backside: isolated

E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM/DSM}$	*max. non-repetitive reverse/forward blocking voltage*		T_{VJ} = 25°C			900	V
$V_{RRM/DRM}$	*max. repetitive reverse/forward blocking voltage*		T_{VJ} = 25°C			800	V
$I_{R/D}$	*reverse current, drain current*	$V_{R/D}$ = 800 V	T_{VJ} = 25°C			200	µA
		$V_{R/D}$ = 800 V	T_{VJ} = 125°C			5	mA
V_T	*forward voltage drop*	I_T = 100 A	T_{VJ} = 25°C			1,26	V
		I_T = 200 A				1,57	V
		I_T = 100 A	T_{VJ} = 125°C			1,24	V
		I_T = 200 A				1,62	V
I_{TAV}	*average forward current*	T_C = 85°C	T_{VJ} = 125°C			60	A
$I_{T(RMS)}$	*RMS forward current*	180° sine				94	A
V_{T0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 125°C			0,85	V
r_T	*slope resistance* } *for power loss calculation only*					3,7	mΩ
R_{thJC}	*thermal resistance junction to case*					0,45	K/W
R_{thCH}	*thermal resistance case to heatsink*				0,2		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			222	W
I_{TSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			1,50	kA
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			1,62	kA
		t = 10 ms; (50 Hz), sine	T_{VJ} = 125°C			1,28	kA
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			1,38	kA
I^2t	*value for fusing*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			11,3	kA²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			10,9	kA²s
		t = 10 ms; (50 Hz), sine	T_{VJ} = 125°C			8,13	kA²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			7,87	kA²s
C_J	*junction capacitance*	V_R = 400V f = 1 MHz	T_{VJ} = 25°C		74		pF
P_{GM}	*max. gate power dissipation*	t_P = 30 µs	T_C = 125°C			10	W
		t_P = 300 µs				5	W
P_{GAV}	*average gate power dissipation*					0,5	W
$(di/dt)_{cr}$	*critical rate of rise of current*	T_{VJ} = 125°C; f = 50 Hz repetitive, I_T = 150 A				150	A/µs
		t_P = 200 µs; di_G/dt = 0,45 A/µs; I_G = 0,45A; V_D = ⅔ V_{DRM} non-repet., I_T = 60 A				500	A/µs
$(dv/dt)_{cr}$	*critical rate of rise of voltage*	V_D = ⅔ V_{DRM}	T_{VJ} = 125°C			1000	V/µs
		R_{GK} = ∞; method 1 (linear voltage rise)					
V_{GT}	*gate trigger voltage*	V_D = 6 V	T_{VJ} = 25°C			1,5	V
			T_{VJ} = -40°C			1,6	V
I_{GT}	*gate trigger current*	V_D = 6 V	T_{VJ} = 25°C			100	mA
			T_{VJ} = -40°C			200	mA
V_{GD}	*gate non-trigger voltage*	V_D = ⅔ V_{DRM}	T_{VJ} = 125°C			0,2	V
I_{GD}	*gate non-trigger current*					10	mA
I_L	*latching current*	t_p = 10 µs	T_{VJ} = 25°C			450	mA
		I_G = 0,45A; di_G/dt = 0,45 A/µs					
I_H	*holding current*	V_D = 6 V R_{GK} = ∞	T_{VJ} = 25°C			200	mA
t_{gd}	*gate controlled delay time*	V_D = ½ V_{DRM}	T_{VJ} = 25°C			2	µs
		I_G = 0,45A; di_G/dt = 0,45 A/µs					
t_q	*turn-off time*	V_R = 100 V; I_T = 150A; V_D = ⅔ V_{DRM}	T_{VJ} =100 °C		150		µs
		di/dt = 10 A/µs; dv/dt = 20 V/µs; t_p = 200 µs					

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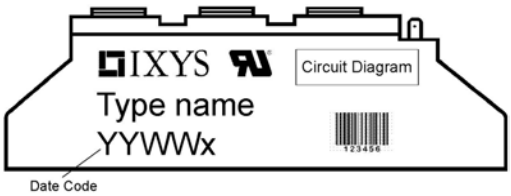
Package	TO-240AA				Ratings			
Symbol	**Definition**	**Conditions**			**min.**	**typ.**	**max.**	**Unit**
I_{RMS}	*RMS current*	per terminal					200	A
T_{VJ}	*virtual junction temperature*				-40		125	°C
T_{op}	*operation temperature*				-40		100	°C
T_{stg}	*storage temperature*				-40		125	°C
Weight						81		g
M_D	*mounting torque*				2,5		4	Nm
M_T	*terminal torque*				2,5		4	Nm
$d_{Spp/App}$	*creepage distance on surface | striking distance through air*		*terminal to terminal*	13,0	9,7			mm
$d_{Spb/Apb}$			*terminal to backside*	16,0	16,0			mm
V_{ISOL}	*isolation voltage*	t = 1 second	50/60 Hz, RMS; I_{ISOL} ≤ 1 mA		4800			V
		t = 1 minute			4000			V

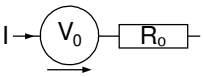


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCD56-08io1B	MCD56-08io1B	Box	36	476463

Similar Part	Package	Voltage class
MCMA65PD1200TB	TO-240AA-1B	1200
MCMA85PD1200TB	TO-240AA-1B	1200

Equivalent Circuits for Simulation

** on die level* T_{VJ} = 125°C



Thyristor

$V_{0\,max}$	*threshold voltage*	0,85	V
$R_{0\,max}$	*slope resistance **	2,5	mΩ

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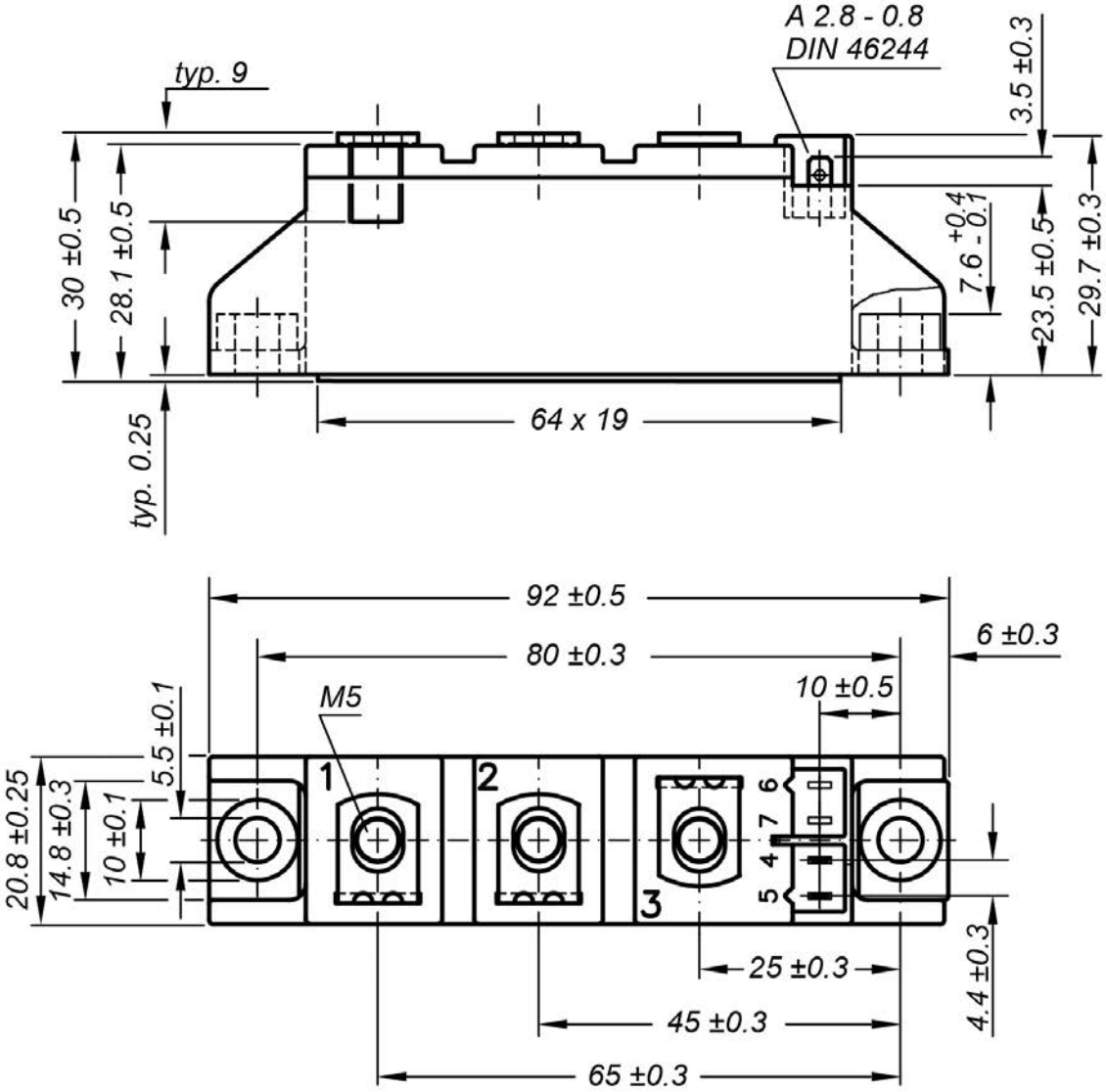
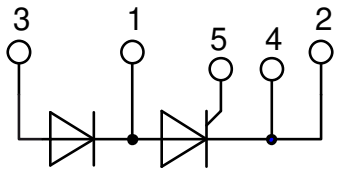
Outlines TO-240AA



Optional accessories for modules
Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red
Type ZY 200L (L = Left for pin pair 4/5) UL 758, style 3751



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Thyristor

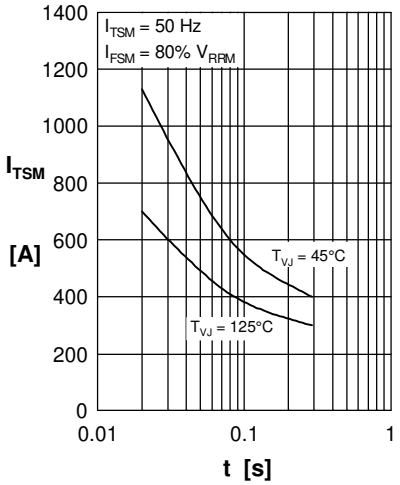

Fig. 1 Surge overload current I_{TSM}, I_{FSM}: Crest value, t: duration

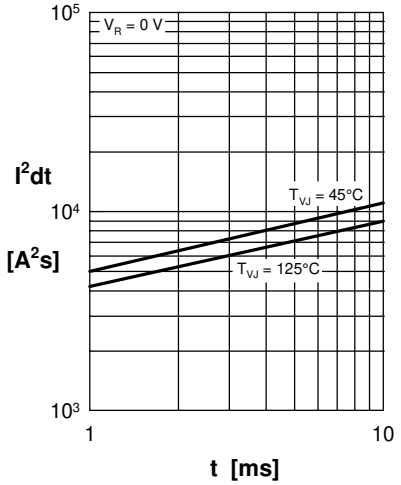

Fig. 2 I^2t versus time (1-10 ms)

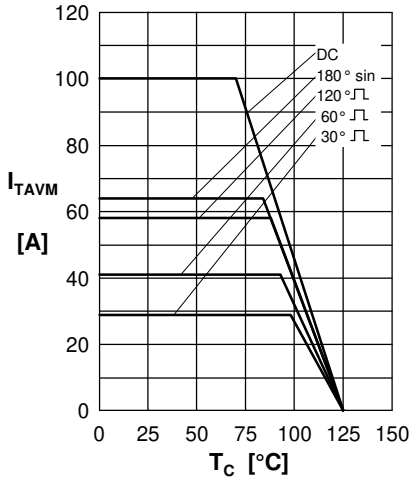

Fig. 3 Max. forward current at case temperature

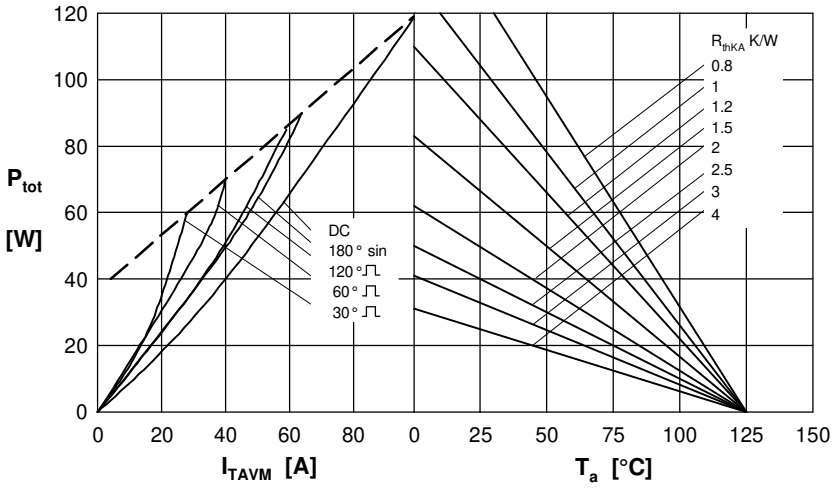

Fig. 4 Power dissipation vs. on-state current & ambient temperature (per thyristor or diode)

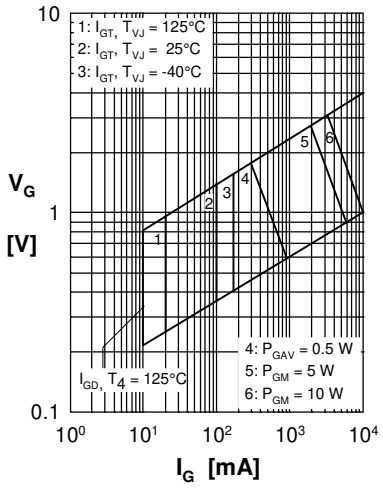

Fig. 5 Gate trigger characteristics

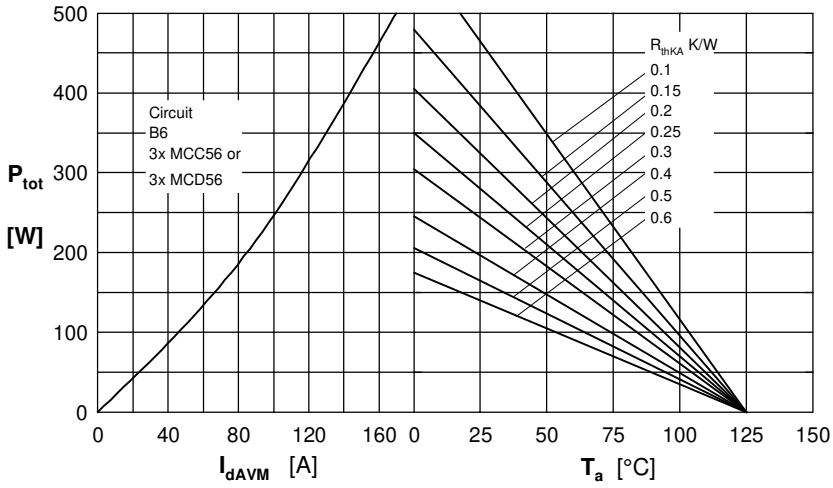

Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

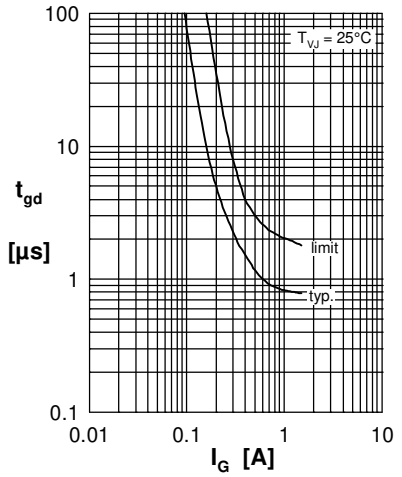

Fig. 7 Gate trigger delay time

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Rectifier

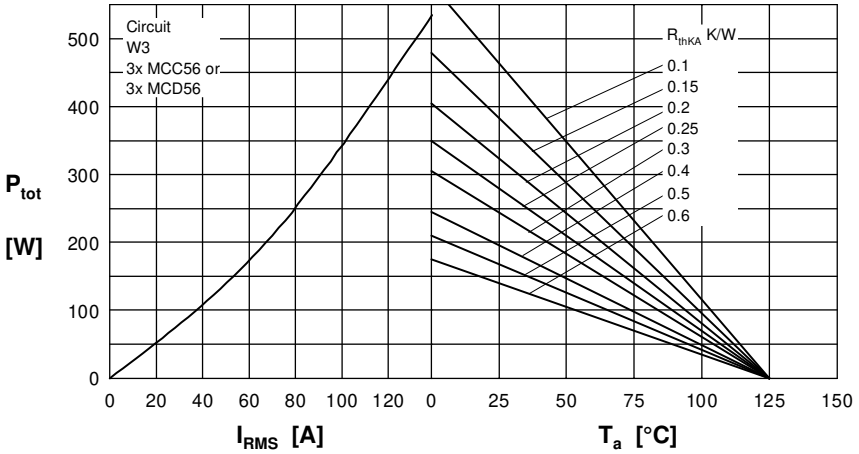
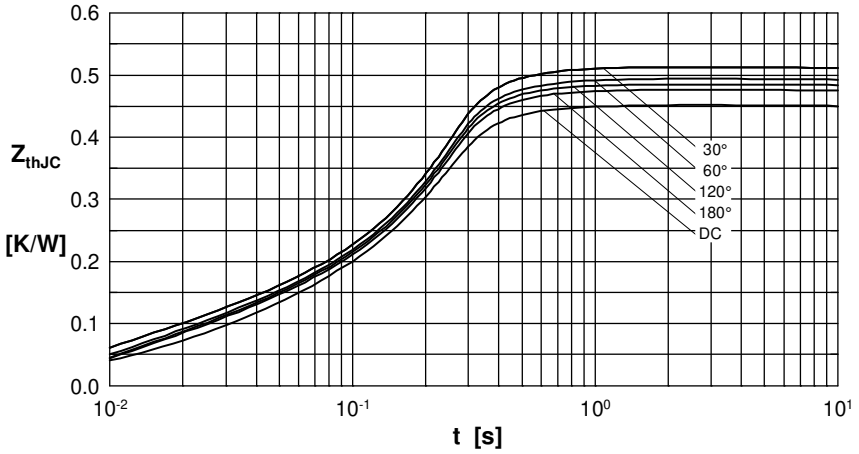


Fig. 8 Three phase AC-controller: Power dissipation versus RMS output current and ambient temperature



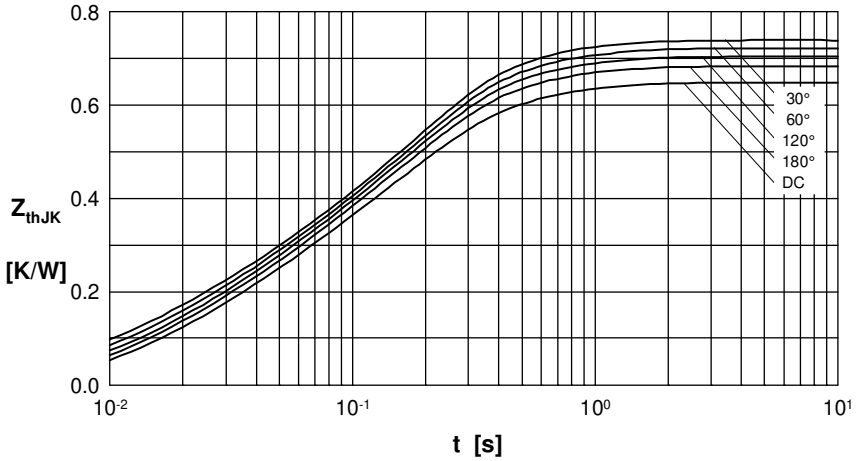
R_{thJC} for various conduction angles d:

d	R_{thJC} [K/W]
DC	0.450
180°	0.470
120°	0.490
60°	0.505
30°	0.520

Constants for Z_{thJC} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.014	0.0150
2	0.026	0.0095
3	0.410	0.1750

Fig. 9 Transient thermal impedance junction to case (per thyristor/diode)



R_{thJK} for various conduction angles d:

d	R_{thJK} [K/W]
DC	0.650
180°	0.670
120°	0.690
60°	0.705
30°	0.720

Constants for Z_{thJK} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.014	0.0150
2	0.026	0.0095
3	0.410	0.1750
4	0.200	0.6700

Fig. 10 Transient thermal impedance junction to heatsink (per thyristor/diode)

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